

HiPerFRED

 V_{RRM} 400 V

=2x 100 A

30 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Parallel legs

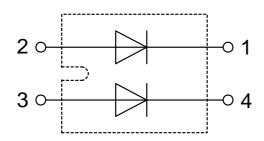
Part number

DSEP2x101-04A



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~ • Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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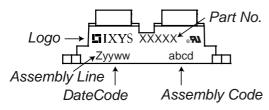


Fast Diode					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocki	ing voltage	$T_{VJ} = 25^{\circ}C$			400	V	
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			400	V	
I _R	reverse current, drain current	$V_R = 400 \text{ V}$	$T_{VJ} = 25^{\circ}C$			1	mA	
		$V_R = 400 \text{ V}$	$T_{VJ} = 150$ °C			4	mΑ	
V _F	forward voltage drop	I _F = 100 A	$T_{VJ} = 25^{\circ}C$			1.54	V	
		$I_F = 200 \text{ A}$				1.95	V	
		$I_F = 100 \text{ A}$	T _{VJ} = 150°C			1.22	V	
		$I_F = 200 \text{ A}$				1.73	V	
I _{FAV}	average forward current	$T_{c} = 45^{\circ}C$	T _{VJ} = 150°C			100	Α	
		rectangular d = 0.5						
V _{F0}	threshold voltage		T _{VJ} = 150°C			0.72	V	
r _F	slope resistance	oss calculation only				5	mΩ	
R_{thJC}	thermal resistance junction to cas	е				0.6	K/W	
R _{thCH}	thermal resistance case to heatsin	nk			0.10		K/W	
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			200	W	
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			1.00	kA	
C _J	junction capacitance	$V_R = 200 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		182		pF	
I _{RM}	max. reverse recovery current	\	$T_{VJ} = 25 ^{\circ}\text{C}$		16		Α	
		$I_F = 100 \text{ A}; V_R = 200 \text{ V}$	$T_{VJ} = 100$ °C		30		Α	
t _{rr}	reverse recovery time	$\begin{cases} I_F = 100 \text{ A}; \ V_R = 200 \text{ V} \\ -di_F / dt = 600 \text{ A/} \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		30		ns	
	•)	$T_{VJ} = 100 ^{\circ}\text{C}$		85		ns	



Package SOT-227B (minibloc)			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					100	Α
T _{VJ}	virtual junction temperature				-40		150	°C
Top	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque			1.1		1.5	Nm	
$\mathbf{M}_{_{T}}$	terminal torque				1.1		1.5	Nm
d _{Spp/App}	araanaga diatanaa an ayufa	and latrifying distance through air	terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}	creepage distance on surfa	ce striking distance through air	terminal to backside 8.6		6.8			mm
V _{ISOL}	isolation voltage	t = 1 second			3000			V
.002		t = 1 minute	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		2500			V

Product Marking



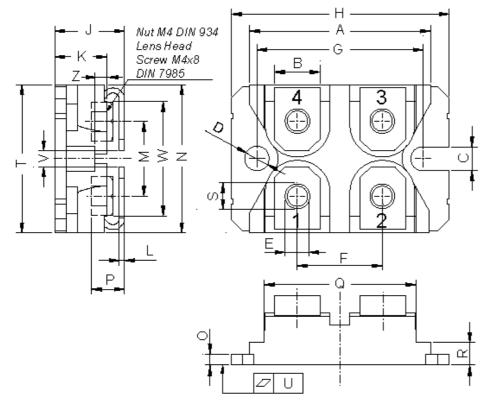
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP2x101-04A	DSEP2x101-04A	Tube	10	484334

Circilar Dant	Darden	Valtana alaas
Similar Part	Package	Voltage class
DPF240X400NA	SOT-227B (minibloc)	400

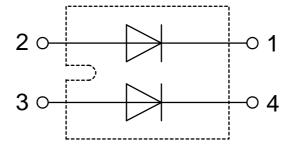
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$	R_0	Fast Diode		
V _{0 max}	threshold voltage	0.72		V
R_{0max}	slope resistance *	4.6		$m\Omega$



Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
DIIII.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
Κ	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	





Fast Diode

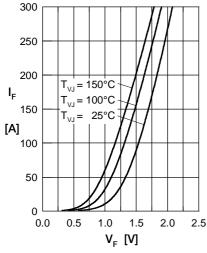


Fig. 1 Forward current I_F versus V_F

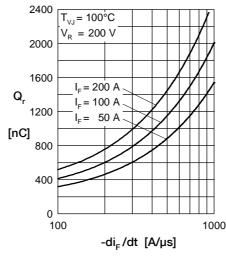


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

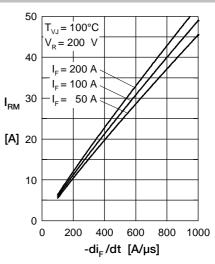


Fig. 3 Typ. peak reverse current $I_{\rm RM}$ versus $-{\rm di_F}/{\rm dt}$

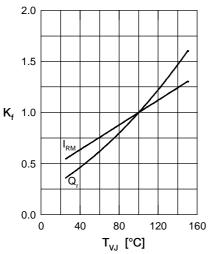


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus T_{VJ}

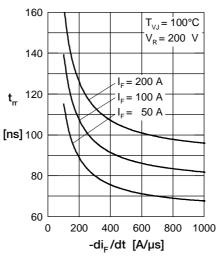


Fig. 5 Typ. recovery time t_{rr} versus $-di_{F}/dt$

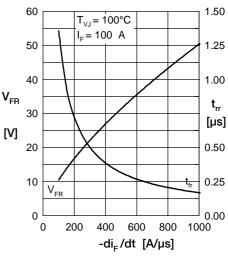


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

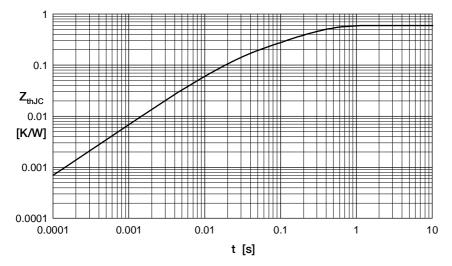


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t _i (s)
1	0.212	0.0055
2	0.248	0.0092
3	0.063	0.0007
4	0.077	0.0391

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